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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/928,975	08/13/2001	Scott Brad Herner	10519-57	7752

7590

08/06/2002

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EXAMINER

MAGEE, THOMAS J

ART UNIT

PAPER NUMBER

2811

DATE MAILED: 08/06/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/928,975

Applicant(s)

HERNER ET AL.

Examiner

Thomas J. Magee

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 28 June 2002.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-8 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-8 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 4.
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other:

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DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of Claims 1 – 8 in Letter No. 7 of June 28, 2002 is acknowledged.

Claim Rejections – 35 U.S.C. 112

2. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

3. Claims 2 – 6 and 8 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to point out and distinctly claim the subject matter which Applicant regards as the invention. The recitation of the term, "invention", in the afore mentioned claims lacks antecedent basis with regard to Claim 1.

Claim Rejections – 35 U.S.C. 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office Action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

5. Claims 1 – 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hu et

al. (US 2002/0045342 A1) in view of Wilson et al. ("Handbook of Multilevel Metallization for Integrated Circuits," Noyes Publ., Westwood, New Jersey (1993), pp. 44 – 50).

6. Regarding Claims 1 and 8, Hu et al. disclose (Page 9, right col., lines 7 – 17) a semiconductor device (memory) structure (with line widths $< 0.25 \mu\text{m}$) comprising: a (doped) silicon layer deposited atop an oxide layer with a non-nucleus (amorphous) silicon layer with incorporated dopants ($< 10^{19}/\text{cm}^3$) and an overlying titanium layer on the non-nucleus layer, which, after annealing forms low resistivity C54 titanium silicide. Hu et al. do not disclose thickness ratios for the silicon/titanium layers, but rather the importance of both thickness and grain size as determinants of resistivity and "fine line effect." This result is further disclosed by Wilson et al., who teach (See Figure 16) that the sheet resistance of titanium silicide (formed by annealing) as a function of initial Ti layer thickness decreases rapidly and reaches a relatively saturated zone for thicknesses > 700 Angstroms, where sheet resistances are less than 3 ohms/square for t greater than approximately 500 Angstroms. Since, in this case, the substrate thickness, t_1 , is large with respect to the layer thickness, t_2 , there is no apparent (t_1/t_2) dependence and the results are almost identical to the graphical data recited by Applicant. Furthermore, if the ratio, t_1/t_2 , is small, it would be obvious that all of the Si would be consumed during annealing, thereby forming a stable platinum silicide contact of low contact resistance.

7. Regarding Claims 2 and 3, there is no statistical difference between values of t_1

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equal to $2.2(t_2)$ and $2.3(t_2) \pm 0.1(t_2)$, hence these claims, as recited, are overlapping and redundant. Further, Hu et al. utilize thicknesses that are comparable to values claimed in Claim 4. It would have been obvious to one having ordinary skill in the art at the time the invention was made to form the silicide layer using the claimed thicknesses of silicon and titanium, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art (In re Aller, 105 USPQ 233).

8. Regarding Claims 5 and 6, Hu et al. disclose the use of doped silicon or polysilicon in the first semiconductor region. Although Hu et al. do not disclose the volume concentration or the dopant, it is commonly known that boron is used as a p-type dopant and it would be obvious to one of ordinary skill in the art to deploy a boron-doped layer to obtain a p-doped material in the word line stack.

9. Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Hu et al. in view of Wilson et al.

Hu et al. disclose a structure of approximately 0.25 μm in width, having a doped first semiconductor region and titanium silicide conductors overlying the first semiconductor region that are all in the low resistivity C54 phase. Although Hu et al. do not disclose the sheet resistances of the Ohmic contacts, it is known (Wilson et al.) for a C54 phase

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titanium silicide layer that for a range of thicknesses the sheet resistances will be less than 3 ohms/square.

Conclusions

10. Any inquiry concerning this communication or earlier communications from the Examiner should be directed to **Thomas Magee**, whose telephone number is **(703) 305 5396**. The Examiner can normally be reached on Monday through Friday from 8:30AM to 5:00PM (EST). If attempts to reach the Examiner by telephone are unsuccessful, the examiner's supervisor, **Tom Thomas**, can be reached on **(703) 308-2772**. The fax number for the organization where this application or proceeding is assigned is **(703) 308-7722**.

Thomas Magee
July 30, 2002


TOM THOMAS
SUPERVISORY PATENT EXAMINER
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